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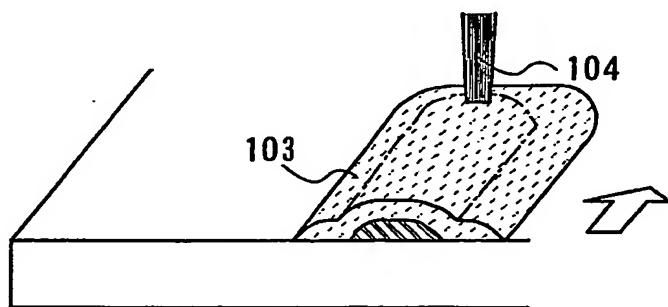
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(54) Title: SEMICONDUCTOR DEVICE, TELEVISION SET, AND METHOD FOR MANUFACTURING THE SAME



(57) Abstract: An object of the invention is
to provide a method for manufacturing a sub-
strate having a film pattern such as an insulat-
ing film, a semiconductor film, or a conductive
film with an easy process, and further, a semi-
conductor device and a television set having a
high throughput or a high yield at low cost and
a manufacturing method thereof. One feature
of the invention is that a first film pattern is
formed by a droplet discharge method, a pho-
tosensitive material is discharged or applied to
the first film pattern, a mask pattern is formed
by irradiating a region where the first film pat-

tern and the photosensitive material are overlapped with a laser beam and by developing, and a second film pattern having a desired
shape is formed by etching the first film pattern using the mask pattern as a mask.

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